NSN 5961-01-650-5134

Diode Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-650-5134 **Inclosure Material:** Plastic **Overall Length:** 1.40 millimeters **Terminal Length:** 0.40 millimeters **Overall Height:** Between 0.45 millimeters and 0.66 millimeters **Overall Width:** 0.60 millimeters **Function For Which Designed:** Bidirectional **End Application:** 228, cont csl **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: Sod-723 molded package **Mounting Method: Terminal Features Provided:** Rohs directive compliance **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 4.7 breakdown voltage, instantaneous **Current Rating Per Characteristic:** 0.5 microamperes drain current **Power Rating Per Characteristic:** 10.0 watts peak pulse output power **Capacitance Rating In Picofarads: Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Product Name:** Low capacitance tvs (transient voltage suppressor) array **Terminal Type And Quantity:** 2 tab, solder lug Shelf Life: N/a

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Unit Of Measure:

NSN 5961-01-650-5134

Diode Semiconductor Device - Page 2 of 2



Demilitarization:

No

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